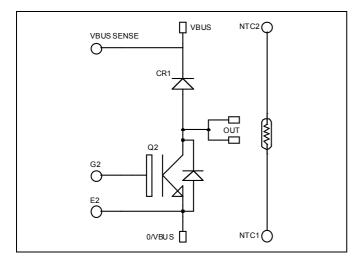


# Boost chopper Fast Trench + Field Stop IGBT® Power Module

$$V_{CES} = 1200V$$
  
 $I_C = 50A @ Tc = 80°C$ 

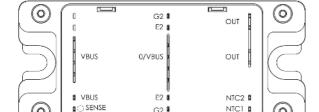


### Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

#### **Features**

- Fast Trench + Field Stop IGBT® Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - Avalanche energy rated
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring



#### **Benefits**

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		1200	V
$I_{C}$	Continuous Collector Current	$T_C = 25^{\circ}C$	75	
1C	Continuous Conector Current	$T_C = 80$ °C	50	A
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	100	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{\mathrm{D}}$	Maximum Power Dissipation	$T_C = 25$ °C	277	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	100A @ 1150V	

These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



### All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μΑ
V	Collector Emitter Saturation Voltage $V_{GE} = 15V$ T		$T_j = 25$ °C		1.7	2.1	V
$V_{CE(sat)}$	Conector Emitter Saturation Voltage	$I_C = 50A$ $T_j = 125$	$T_j = 125$ °C		2.0		·
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 2mA$		5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

**Dynamic Characteristics** 

•	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0V$		3600		
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$		190		pF
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz		160		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		90		
$T_{\rm r}$	Rise Time	$V_{GE} = 15V$		30		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 50A$		420		ns
$T_{\mathrm{f}}$	Fall Time	$R_G = 18 \Omega$		70		1
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)		90		
$T_{r}$	Rise Time	$V_{GE} = 15V$		50		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 50A$		520		ns
$T_{\rm f}$	Fall Time	$R_G = 18 \Omega$		90		
Eon	Turn-on Switching Energy	$V_{GE} = 15V \ V_{Bus} = 600V$ $T_j = 125^{\circ}C$		5		m I
$E_{\text{off}}$	Turn-off Switching Energy	$I_C = 50A$ $R_G = 18 \Omega$ $T_j = 125^{\circ}C$		5.5		mJ

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			1200			V
T	Maximum Reverse Leakage Current	$V_{R}=1200V$	$T_j = 25^{\circ}C$			250	^
$I_{RM}$	Waximum Reverse Leakage Current	V <sub>R</sub> -1200 V	$T_j = 125$ °C			500	μA
$I_{\mathrm{F}}$	DC Forward Current		$Tc = 80^{\circ}C$		50		A
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 50A$	$T_i = 25^{\circ}C$		1.4	1.9	V
<b>V</b> F	Blode I of ward Voltage	1 <sub>F</sub> 3071	$T_{i} = 125^{\circ}C$		1.3		<b>,</b>
t <sub>rr</sub>	Reverse Recovery Time		$T_j = 25^{\circ}C$		150		ns
۲r	Reverse Recovery Time		$T_{j} = 125^{\circ}C$		250		115
0	Reverse Recovery Charge	$I_F = 50A$ $V_R = 600V$	$T_j = 25^{\circ}C$		4.5		μC
$Q_{rr}$	Reverse Recovery Charge	$di/dt = 2000 \text{ A/} \mu \text{s}$	$T_{j} = 125^{\circ}C$		9		μС
E <sub>r</sub>	Reverse Recovery Energy	·	$T_j = 25$ °C		2.1		mJ
$\mathbf{L}_{\mathbf{r}}$	Reverse Recovery Energy		$T_{j} = 125^{\circ}C$		4.2		1113



 $Temperature\ sensor\ NTC\ (see\ application\ note\ APT0406\ on\ www.microsemi.com\ for\ more\ information).$ 

Symbol	Characteristic	Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

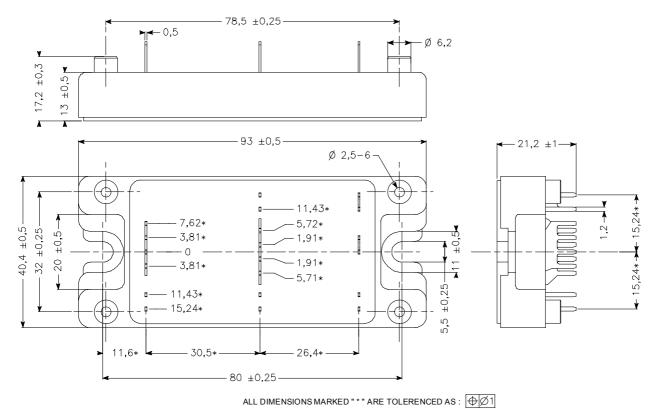
$$R_{T} = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

$$R_{T}: \text{ Thermistor value at T}$$

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
$R_{thJC}$	Junction to Case Thermal Resistance		IGBT			0.45	°C/W
IX <sub>th</sub> JC			Diode			0.58	C/ <b>VV</b>
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range Storage Temperature Range		-40		150		
$T_{STG}$			-40		125	°C	
$T_{\rm C}$	Operating Case Temperature		-40		100		
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight				160	g	

### SP4 Package outline (dimensions in mm)



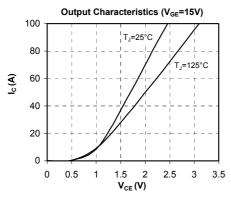
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

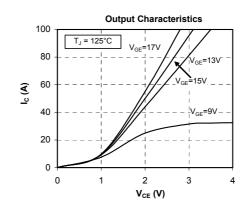
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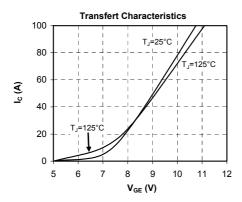
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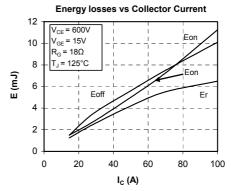


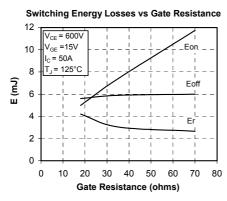
### **Typical Performance Curve**

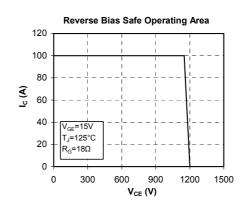


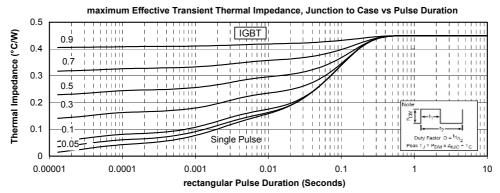




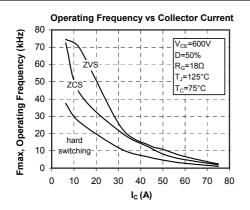


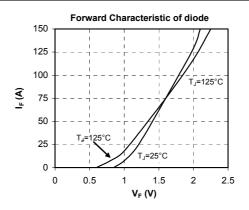


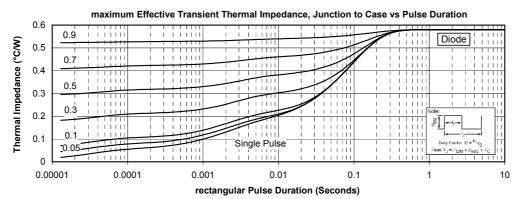














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